Description

The MMDT3906 is a dual PNP epitaxial planar transistor packaged in SOT-363, designed for low-power signal amplification and switching applications in compact circuit designs. It features stable electrical performance and small form factor for space-constrained layouts.

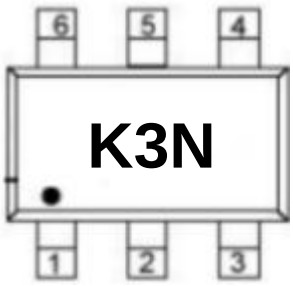
Features

- Dual PNP transistor configuration
- Epitaxial planar die construction
- Optimized for low-power amplification and switching
- SOT-363 miniature surface mount package
- RoHS compliant

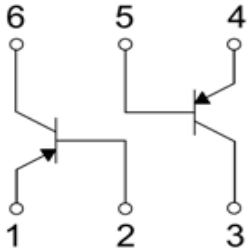
Application

- Portable consumer electronics
- Low-power signal switching circuits
- Small-signal amplification modules
- High-density PCB designs
- Battery-powered devices

Marking Diagram



Circuit Diagram



Ordering information

DEVICE	PACKAGE
MMDT3906	3000/Tape & Reel

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Maximum Ratings (T_A=25℃)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.2	A
P_C	Collector Power Dissipation	0.2	W
$R_{\theta JA}$	Thermal Resistance. Junction to Ambient Air	625	℃/W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

Electrical Characteristics (T_A=25℃)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA,I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-5			V
Collector cut-off current	I_{CEX}	V_{CE}=-30V,$V_{EB(OFF)}$=-3V			-50	nA
Base cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-50	nA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V,I_C=-0.1mA	60			
	$h_{FE(2)}$	V_{CE}=-1V,I_C=-1mA	80			
	$h_{FE(3)}$	V_{CE}=-1V,I_C=-10mA	100		300	
	$h_{FE(4)}$	V_{CE}=-1V,I_C=-50mA	60			
	$h_{FE(5)}$	V_{CE}=-1V,I_C=-100mA	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	I_C=-10mA,I_B=-1mA			-0.25	V
	$V_{CE(sat)2}$	I_C=-50mA,I_B=-5mA			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	I_C=-10mA,I_B=-1mA	-0.65		-0.85	V
	$V_{BE(sat)2}$	I_C=-50mA,I_B=-5mA			-0.95	V
Transition frequency	f_T	V_{CE}=-20V,I_C=-10mA,f=100MHz	250			MHz
Collector output capacitance	C_{ob}	V_{CB}=-5V,I_E=0,f=1MHz			4.5	pF
Noise figure	NF	V_{CE}=-5V,I_c=-0.1mA,f=1KHz,R_g=1KΩ			4	dB
Delay time	t_d	V_{CC}=-3V, V_{BE}=0.5V I_C=-10mA , I_{B1}=-I_{B2}=-1mA			35	nS
Rise time	t_r				35	nS
Storage time	t_S	V_{CC}=-3V, I_C=-10mA I_{B1}=-I_{B2}=- 1mA			225	nS
Fall time	t_f				75	nS

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Typical Performance Curves

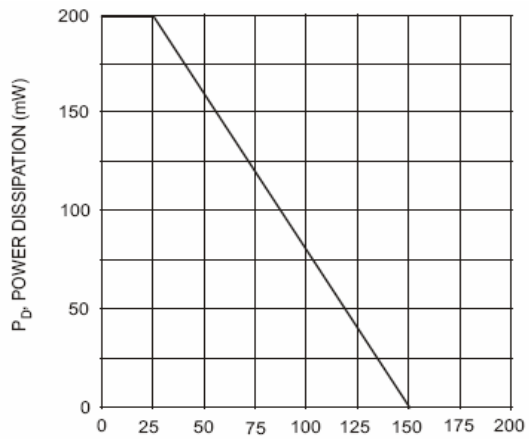


Fig. 1, Max Power Dissipation vs Ambient Temperature

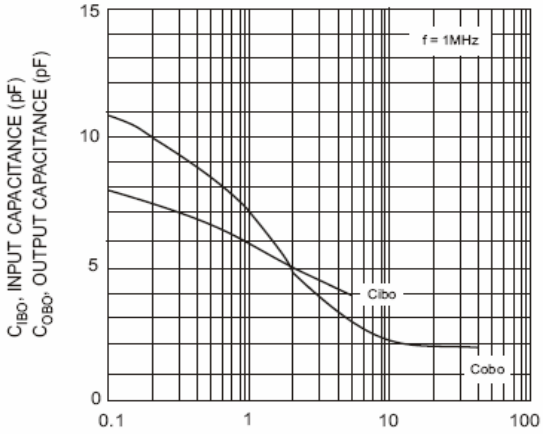


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

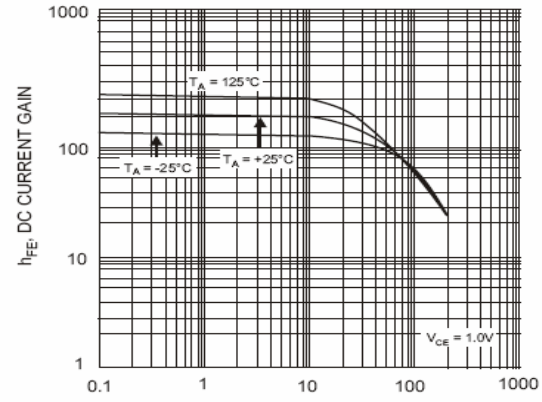


Fig. 3, Typical DC Current Gain vs Collector Current

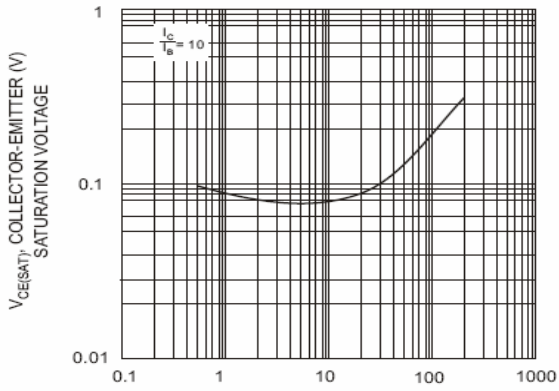


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

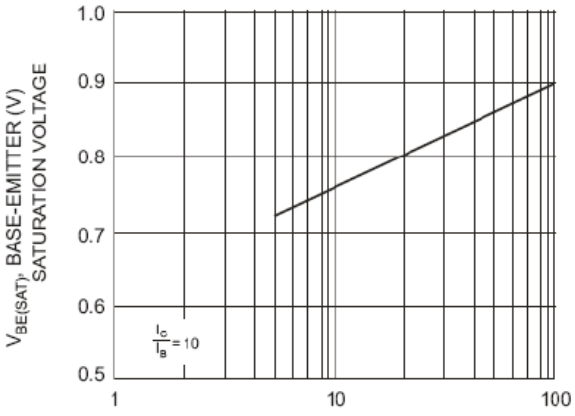
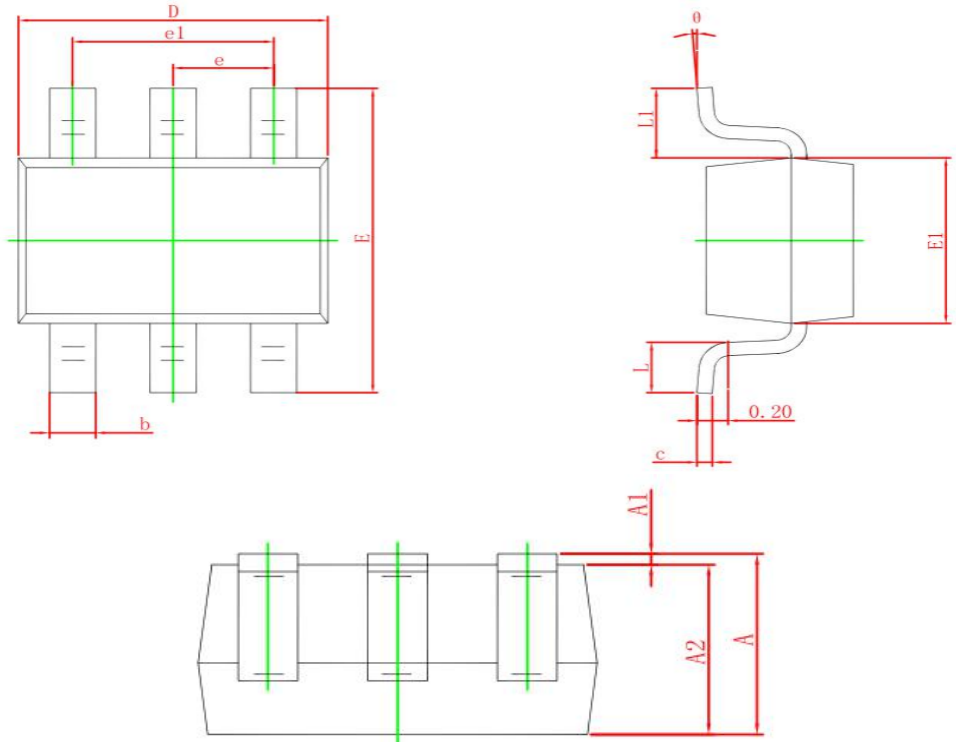


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

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SOT-363 Package Outline Dimensions



Symbol	Dim in mm		
	Min	Nor	Max
A	0.90	1.00	1.10
A1	0.00	0.05	0.10
A2	0.90	0.95	1.00
b	0.15	0.25	0.35
c	0.08	0.12	0.15
D	2.05	2.10	2.25
E	2.15	2.30	2.45
E1	1.15	1.25	1.35
e	0.650TPY.		
e1	1.2	1.3	1.4
L	0.26	0.36	0.46
L1	0.525REF.		
θ	0°	4°	8°

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